优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D T_A = +25°C
25V	4Ω @ V_{GS} = 4.5V	0.26A
	5Ω @ V_{GS} = 2.7V	0.23A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.

Features

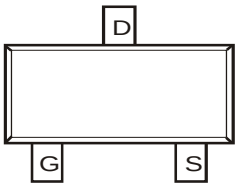
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate (>6kV Human Body Model)

Mechanical Data

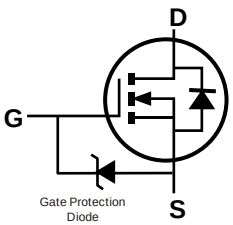
- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Solderable per MIL-STD-202, Method 208 e3
- Lead Free Plating (Matte Tin Finish Annealed over Alloy 42 Leadframe).
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

ESD HBM >6kV

Top View



Top View
Pin Configuration



Equivalent Circuit

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	25	V
Gate-Source Voltage			V_{GSS}	8	V
Continuous Drain Current (Note 6) V_{GS} = 4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	0.26 0.21	A
Continuous Drain Current (Note 6) V_{GS} = 2.7V	Steady State	T_A = +25°C T_A = +70°C	I_D	0.23 0.18	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I_{DM}	1.5	A
Maximum Body Diode Continuous Current (Note 6)			I_S	0.5	A

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation	(Note 5)	P_D	0.32	W
	(Note 6)		0.4	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	369	°C/W
	(Note 6)		296	
Thermal Resistance, Junction to Case	(Note 6)	$R_{\theta JC}$	115	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	25	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0	µA	V_{DS} = 20V, V_{GS} = 0V
Gate-Body Leakage	I_{GSS}	—	—	100	nA	V_{GS} = 8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	0.7	—	1.1	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	—	4	Ω	V_{GS} = 4.5V, I_D = 0.4A
		—	—	5	Ω	V_{GS} = 2.7V, I_D = 0.2A
Forward Transconductance	g_{FS}	—	1	—	S	V_{DS} = 5V, I_D = 0.4A
Diode Forward Voltage	V_{SD}	—	0.76	1.2	V	V_{GS} = 0V, I_S = 0.29A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	27.9	42	pF	V_{DS} = 10V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	6.1	9.2		
Reverse Transfer Capacitance	C_{rss}	—	2.0	3.0		
Gate Resistance	R_G	—	26.4	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	0.36	—	nC	V_{GS} = 4.5V, V_{DS} = 5V, I_D = 0.2A
Gate-Source Charge	Q_{gs}	—	0.06	—		
Gate-Drain Charge	Q_{gd}	—	0.04	—		
Turn-On Delay Time	$t_{D(on)}$	—	2.9	—	nS	V_{GS} = 4.5V, V_{DS} = 6V I_D = 0.5A, R_G = 50Ω
Turn-On Rise Time	t_r	—	1.8	—		
Turn-Off Delay Time	$t_{D(off)}$	—	6.6	—		
Turn-Off Fall Time	t_f	—	2.3	—		

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout
7 .Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

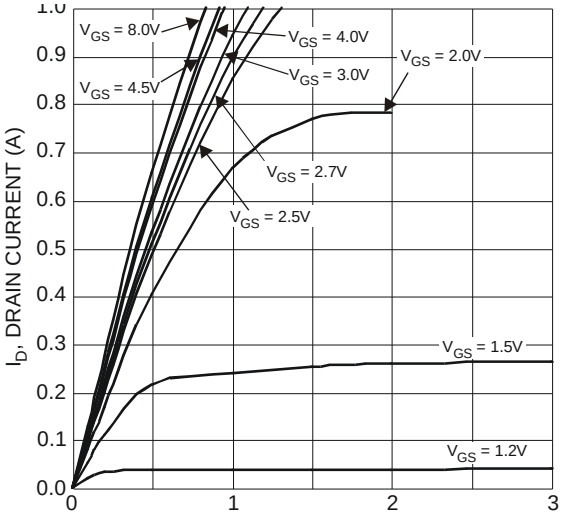


Figure 1 Typical Output Characteristics

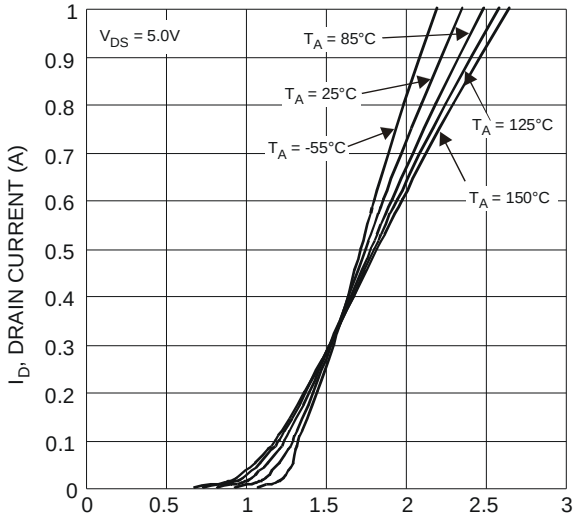


Figure 2 Typical Transfer Characteristics

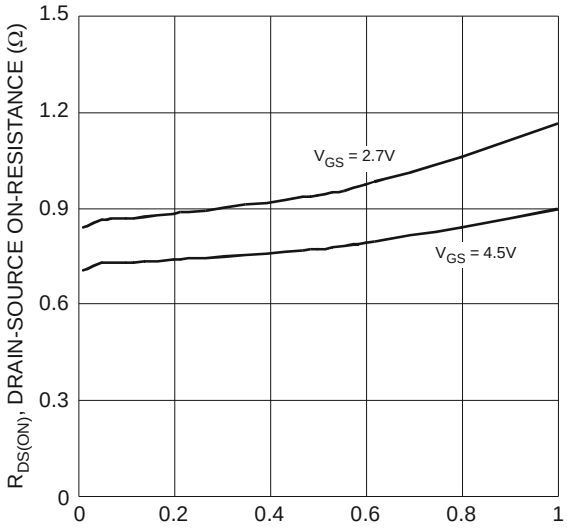


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

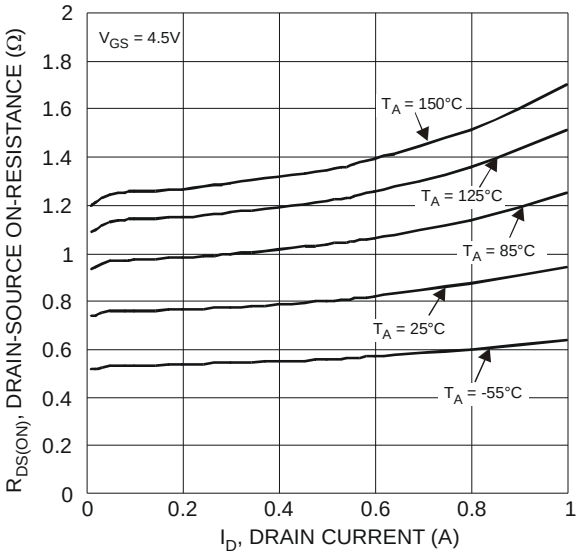


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

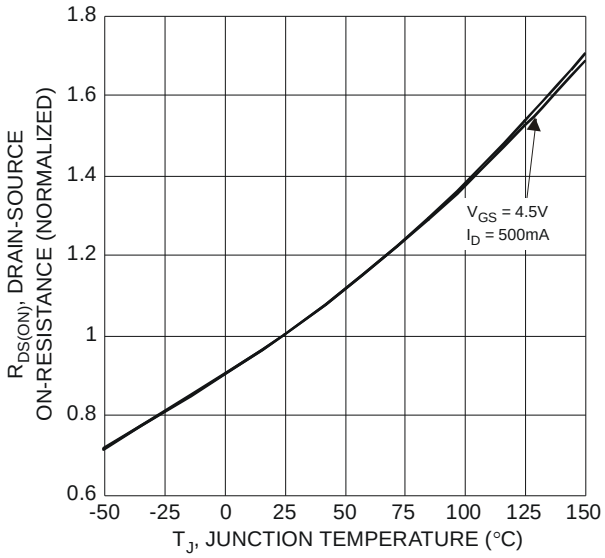


Figure 5 On-Resistance Variation with Temperature

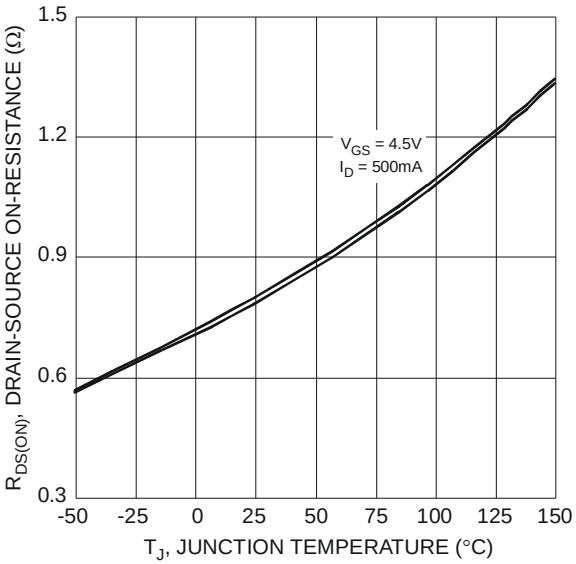


Figure 6 On-Resistance Variation with Temperature

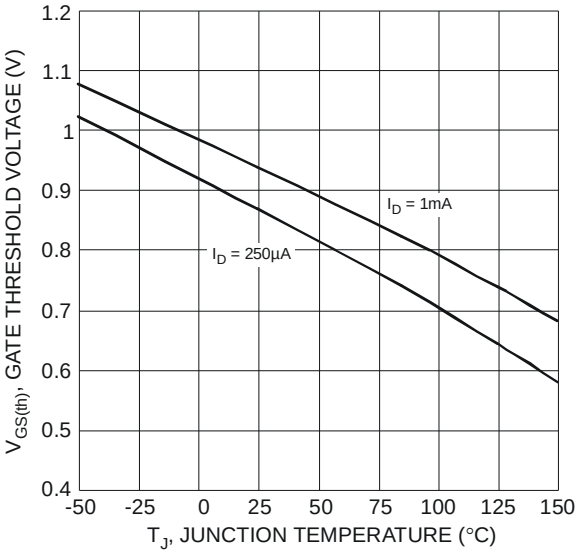


Figure 7 Gate Threshold Variation vs. Ambient Temperature

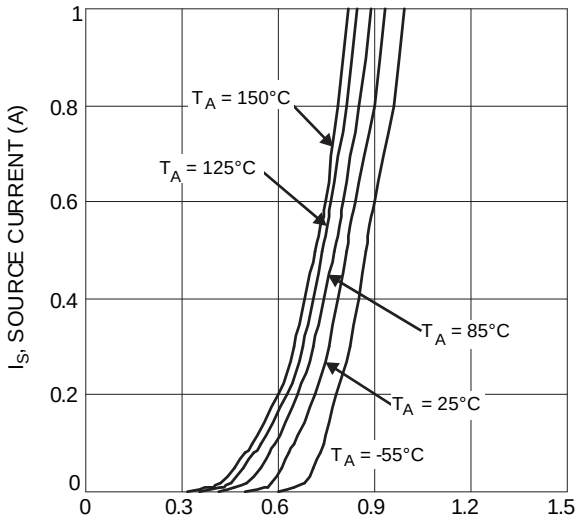


Figure 8 Diode Forward Voltage vs. Current

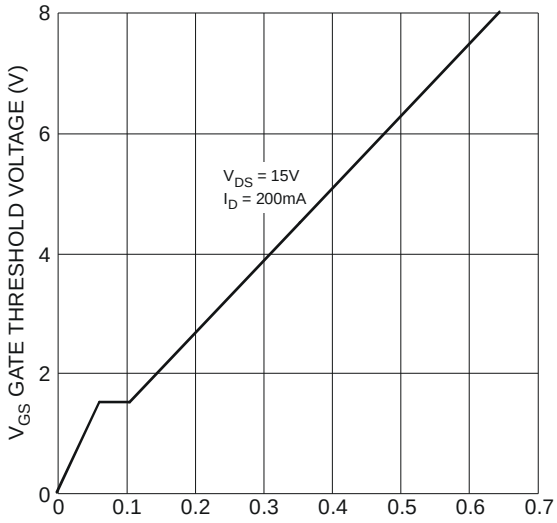


Figure 9 Gate Charge

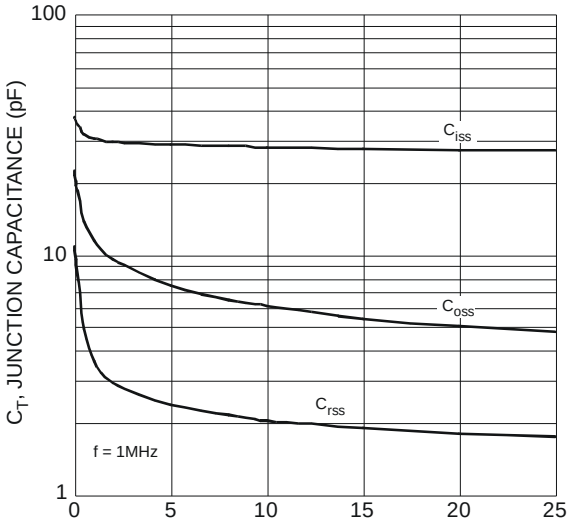


Figure 10 Typical Junction Capacitance

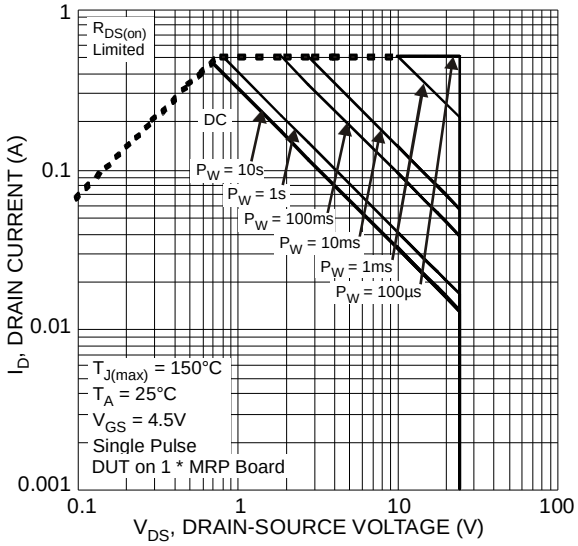


Figure 11 SOA, Safe Operation Area

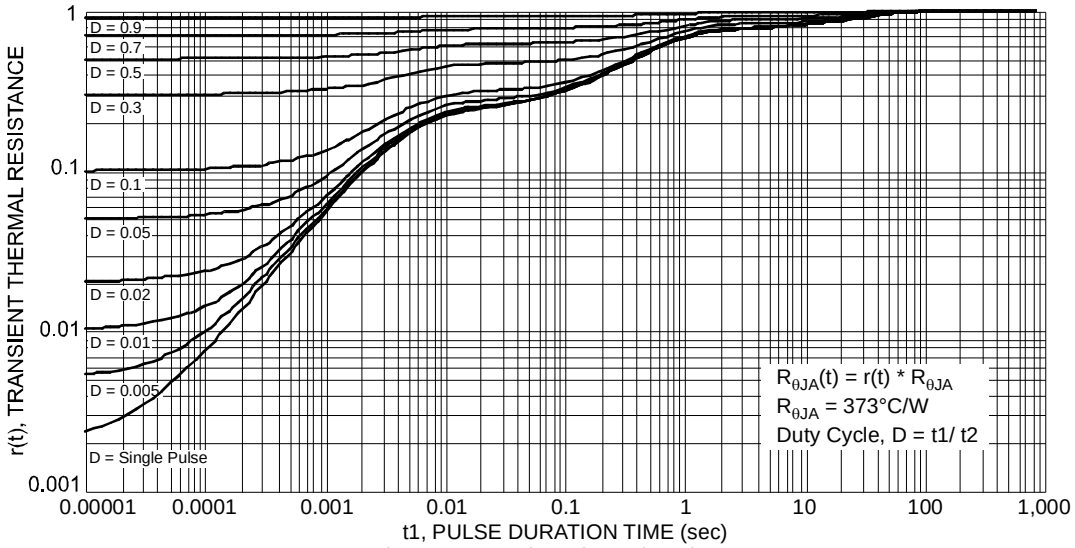
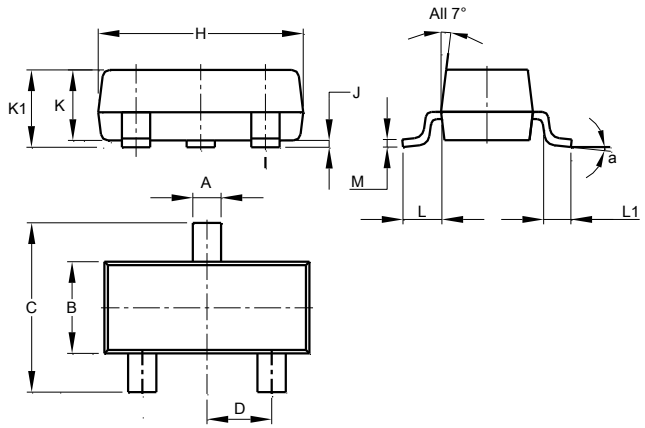


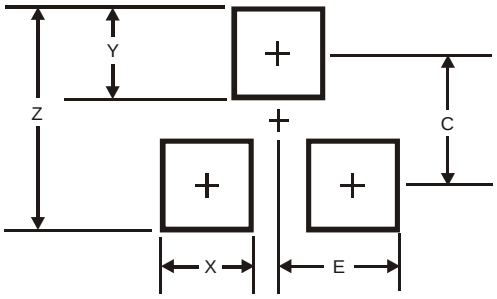
Figure 12 Transient Thermal Resistance

Package Outline Dimensions



SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	8°		
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35